



# SINGLE BUFFER

- HIGH SPEED:  $t_{PD} = 3.6$ ns (TYP.) at  $V_{CC} = 5$ V
- LOW POWER DISSIPATION:  $I_{CC} = 1\mu A(MAX.)$  at  $T_A=25^{\circ}C$
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (MIN.)
- POWER DOWN PROTECTION ON INPUT
- SYMMETRICAL OUTPUT IMPEDANCE:  $|I_{OH}| = I_{OL} = 8\text{mA}$  (MIN) at  $V_{CC} = 4.5\text{V}$
- BALANCED PROPAGATION DELAYS: t<sub>PLH</sub> ≅ t<sub>PHL</sub>
- OPERATING VOLTAGE RANGE: V<sub>CC</sub>(OPR) = 2V to 5.5V
- IMPROVED LATCH-UP IMMUNITY



The 74V1G70 is an advanced high-speed CMOS SINGLE BUFFER fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

The internal circuit is composed of 2 stages including buffer output, which provide high noise immunity and stable output.

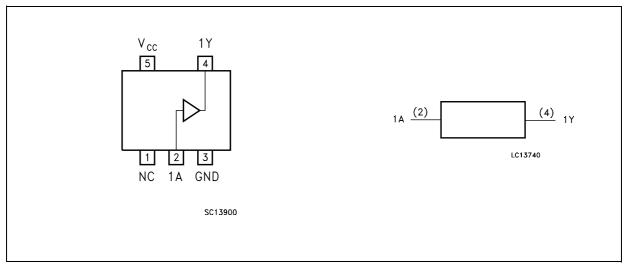


#### **ORDER CODES**

PACKAGE	T&R
SOT23-5L	74V1G70STR
SOT323-5L	74V1G70CTR

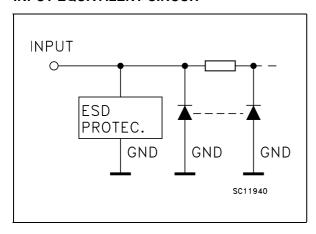
Power down protection is provided on input and 0 to 7V can be accepted on input with no regard to the supply voltage. This device can be used to interface 5V to 3V.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



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#### **INPUT EQUIVALENT CIRCUIT**



#### **PIN DESCRIPTION**

PIN N°	SYMBOL	NAME AND FUNCTION
1	NC	Not Connected
2	1A	Data Input
4	1Y	Data Output
3	GND	Ground (0V)
5	V <sub>CC</sub>	Positive Supply Voltage

#### **TRUTH TABLE**

Α	Y
L	L
Н	Н

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	2 to 5.5	V
VI	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) ( $V_{CC}$ = 3.3 $\pm$ 0.3V) ( $V_{CC}$ = 5.0 $\pm$ 0.5V)	0 to 100 0 to 20	ns/V ns/V

<sup>1)</sup>  $V_{IN}$  from 30% to 70% of  $V_{CC}$ 

#### **DC SPECIFICATIONS**

		Test Condition		Value							
Symbol	Symbol Parameter			T <sub>A</sub> = 25°C			-40 to	85°C	-55 to	125°C	Unit
		V <sub>CC</sub> (V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	3.0 to 5.5		0.7V <sub>CC</sub>			0.7V <sub>CC</sub>		0.7V <sub>CC</sub>		V
$V_{IL}$	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	3.0 to 5.5				0.3V <sub>CC</sub>		0.3V <sub>CC</sub>		0.3V <sub>CC</sub>	V
V <sub>OH</sub>	High Level Output	2.0	I <sub>O</sub> =-50 μA	1.9	2.0		1.9		1.9		
	Voltage	3.0	I <sub>O</sub> =-50 μA	2.9	3.0		2.9		2.9		
		4.5	I <sub>O</sub> =-50 μA	4.4	4.5		4.4		4.4		V
		3.0	I <sub>O</sub> =-4 mA	2.58			2.48		2.4		
		4.5	I <sub>O</sub> =-8 mA	3.94			3.8		3.7		
V <sub>OL</sub>	Low Level Output	2.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	
	Voltage	3.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	
		4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I <sub>O</sub> =4 mA			0.36		0.44		0.55	
		4.5	I <sub>O</sub> =8 mA			0.36		0.44		0.55	
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			± 0.1		± 1		± 1	μΑ
I <sub>CC</sub>	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

		Test Condition		Value								
Symbol	Parameter	V <sub>CC</sub>	CL		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		V <sub>CC</sub>	(pF)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay	3.3 <sup>(*)</sup>	15			4.8	7.0	1.0	8.0	1.0	9.0	
	Time	3.3 <sup>(*)</sup>	50			5.3	8.0	1.0	9.0	1.0	10.0	ns
	5.0 <sup>(**)</sup>	15			3.6	5.5	1.0	6.5	1.0	7.5	115	
		5.0 <sup>(**)</sup>	50			4.0	6.0	1.0	7.0	1.0	8.0	

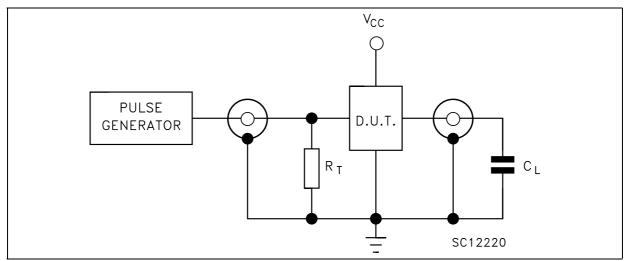
<sup>(\*)</sup> Voltage range is  $3.3V \pm 0.3V$  (\*\*) Voltage range is  $5.0V \pm 0.5V$ 

## **CAPACITIVE CHARACTERISTICS**

		Test Condition		Value						
Symbol	Parameter		T <sub>A</sub> = 25°C -40 to 85°C -55 to 125°		125°C	Unit				
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance			4	10		10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)			10						pF

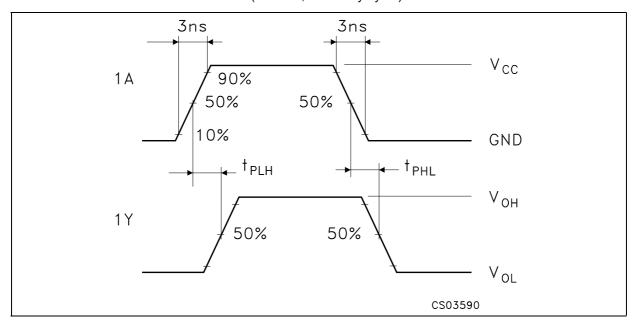
<sup>1)</sup> C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> x V<sub>CC</sub> x f<sub>IN</sub> + I<sub>CC</sub>

#### **TEST CIRCUIT**



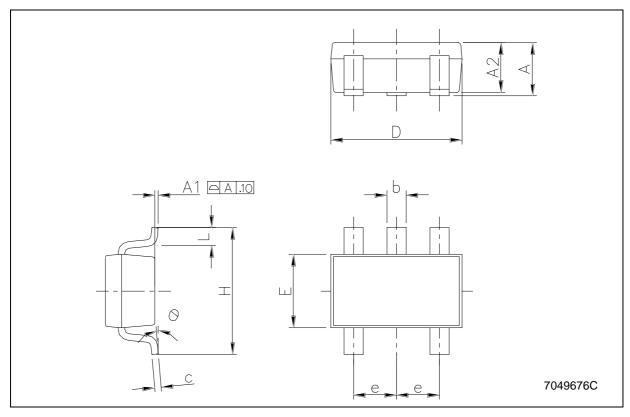
 $C_L$  =15/50pF or equivalent (includes jig and probe capacitance)  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

### WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



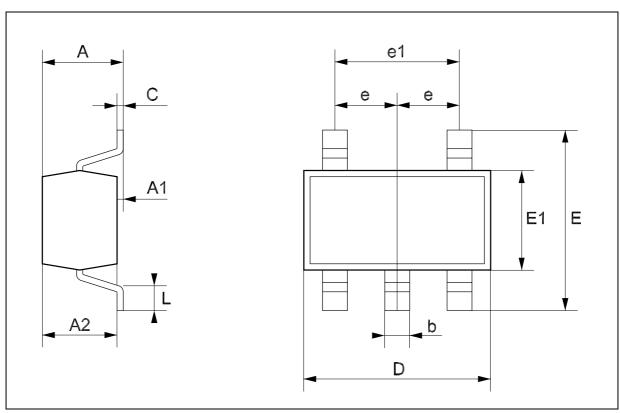
# **SOT23-5L MECHANICAL DATA**

DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	0.90		1.45	35.4		57.1
A1	0.00		0.10	0.0		3.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
С	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	1.50		1.75	59.0		68.8
е		0.95			37.4	
Н	2.60		3.00	102.3		118.1
L	0.10		0.60	3.9		23.6

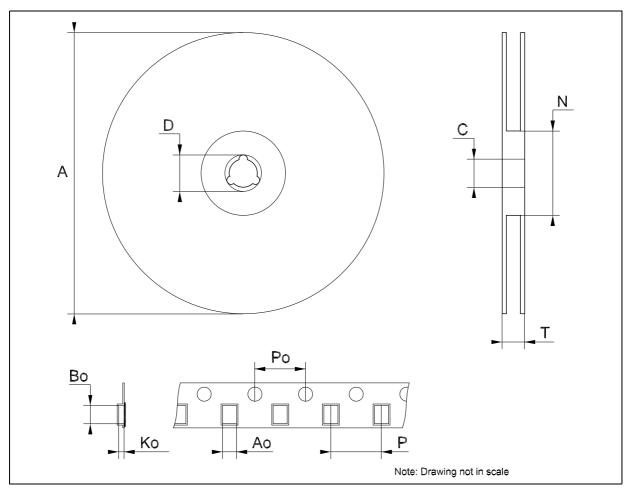


# **SOT323-5L MECHANICAL DATA**

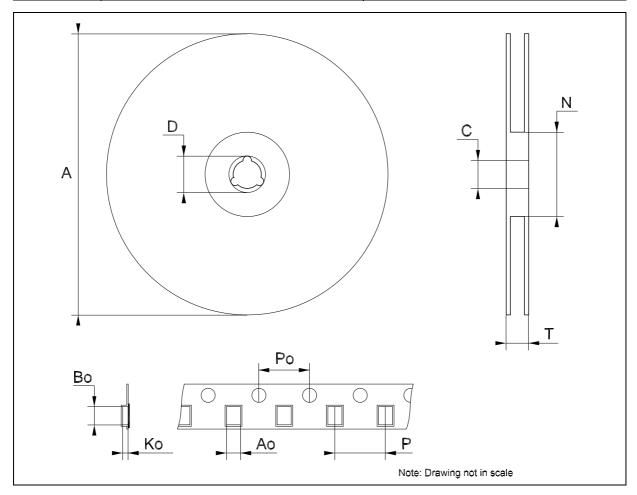
DIM.		mm.			mils		
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.80		1.10	31.5		43.3	
A1	0.00		0.10	0.0		3.9	
A2	0.80		1.00	31.5		39.4	
b	0.15		0.30	5.9		11.8	
С	0.10		0.18	3.9		7.1	
D	1.80		2.20	70.9		86.6	
E	1.80		2.40	70.9		94.5	
E1	1.15		1.35	45.3		53.1	
е		0 .65			25.6		
e1		1.3			51.2		
L	0.10		0.30	3.9		11.8	



DIM		mm.			inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			180			7.086	
С	12.8	13.0	13.2	0.504	0.512	0.519	
D	20.2			0.795			
N	60			2.362			
Т			14.4			0.567	
Ao	3.13	3.23	3.33	0.123	0.127	0.131	
Во	3.07	3.17	3.27	0.120	0.124	0.128	
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58	
Po	3.9	4.0	4.1	0.153	0.157	0.161	
Р	3.9	4.0	4.1	0.153	0.157	0.161	



DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	175	180	185	6.889	7.086	7.283
С	12.8	13	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	59.5	60	60.5		2.362	
Т			14.4			0.567
Ao		2.25			0.088	
Во		2.7			0.106	
Ko		1.2			0.047	
Ро	3.9	4	4.1	0.153	0.157	0.161
Р	3.8	4	4.2	0.149	0.157	0.165



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